

シリコンNPN三重拡散プレーナ型トランジスタ(2SB1382とコンプリメンタリ)

用途: ソレノイド、モータ駆動、一般用

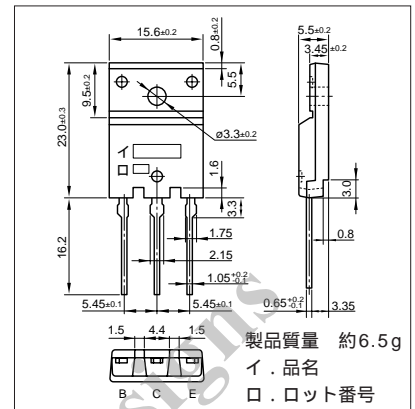
絶対最大定格 (Ta = 25)

記号	規格値	単位
VcBO	120	V
VCEO	120	V
VEBO	6	V
Ic	16(パルス26)	A
Ib	1	A
Pc	75(Tc = 25)	W
Tj	150	
Tstg	-55 ~ +150	

電気的特性 (Ta = 25)

記号	試験条件	規格値	単位
ICBO	V _{CB} = 120V	10max	μA
IEBO	V _{EB} = 6V	10max	mA
V(BR)CEO	I _c = 10mA	120min	V
hFE	V _{CE} = 4V, I _c = 8A	2000min	
V _{CE(sat)}	I _c = 8A, I _b = 16mA	1.5max	V
V _{BE(sat)}	I _c = 8A, I _b = 16mA	2.5max	V
f _T	V _{CE} = 12V, I _E = -1A	20typ	MHz
C _{OB}	V _{CB} = 10V, f = 1MHz	210typ	pF

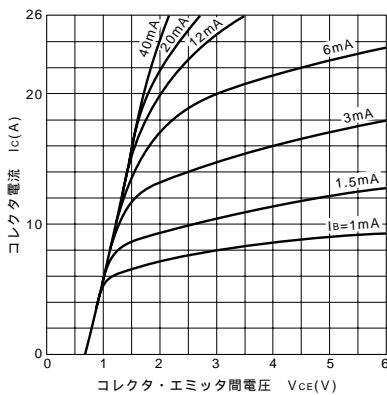
外形図 FM100(T03PF)



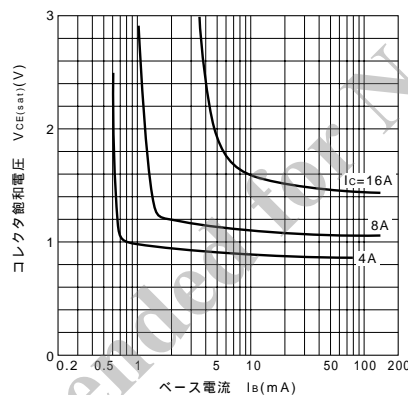
代表的スイッチング特性 (エミッタ接地)

V _{CC} (V)	R _L (Ω)	I _c (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (mA)	I _{B2} (mA)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
40	5	8	10	5	16	16	0.6typ	7.0typ	1.5typ

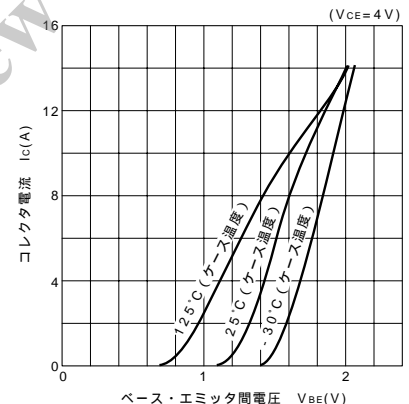
I_c-V_{CE}特性 (代表例)



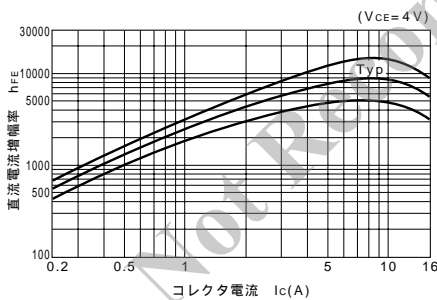
V_{CE(sat)}-I_b特性 (代表例)



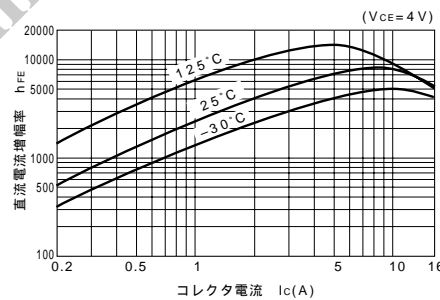
I_c-V_{BE}温度特性 (代表例)



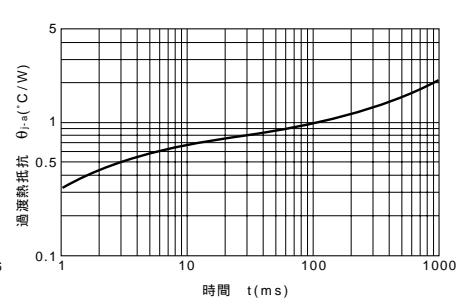
h_{FE}-I_c特性 (代表例)



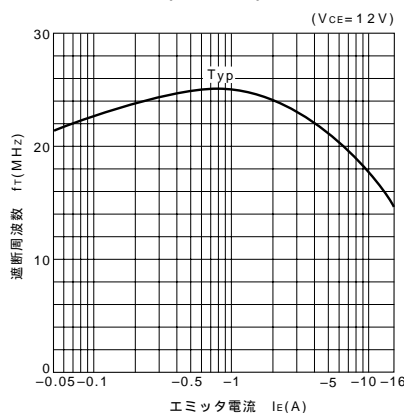
h_{FE}-I_c温度特性 (代表例)



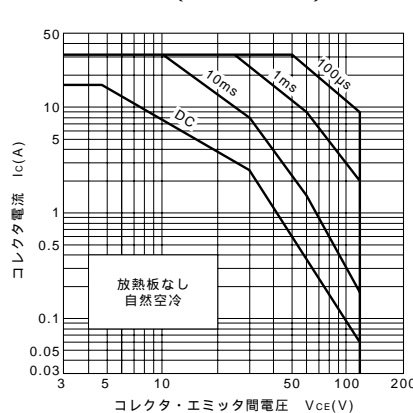
θ_{JA}-t特性



f_T-I_E特性 (代表例)



ASO曲線 (単発パルス)



P_c-Ta定格

